Japanese Equivalent JFET Types

SILICON JUNCTION FIELD–EFFECT TRANSISTORS

			Japanese	2SK17	2SK40	2SK59	2SK105
			InterFET	IFN17	IFN40	IFN59	IFN105
			Process	NJ16	NJ16	NJ16	NJ16
Parameters	**Conditions**	**Unit Limit**		**N Channel**	**N Channel**	**N Channel**	**N Channel**
BV_{GSS}	I_G = – 1.0 µA	V Min		– 20	– 50	– 30	– 50
I_{GSS}	V_{GS} = ( ), V_{DS} = Ø	nA Max		0.10 (– 10 V)	1.0 (– 30 V)	1.0 (– 10 V)	1.0 (– 30 V)
$V_{GS(off)}$	V_{DS} = ( ), I_D = 1.0 nA	V Min/Max		– 0.5/– 6.0 (10 V)	– 0.4/– 5.0 (15 V)	– 0.4/– 5.0 (10 V)	– 0.25/– 4.5 (5.0 V)
I_{DSS}	V_{DS} = ( ), V_{GS} = Ø	mA Min/Max		0.3/6.5 (10 V)	0.6/6.5 (15 V)	0.3/1.4 (10 V)	0.5/12 (5.0 V)
gfs	V_{DS} = ( ), V_{GS} = Ø	mS Typ		2.0 (10 V)	2.0 (15 V)	1.5 (10 V)	2.1 (5.0 V)
C_{iss}	V_{GS} = ( ), V_{DS} = ( )	pF Typ		4.0 (Ø) (Ø)	4.0 (Ø) (15 V)		4.0 (Ø) (10 V)
C_{rss}	V_{GS} = ( ), V_{DS} = ( )	pF Typ		1.2 (– 10 V) (Ø)	1.2 (Ø) (15 V)		1.0 (Ø) (10 V)
			Package Configuration	TO– 226	TO– 226	TO– 226	TO– 226
			Pin Configuration	SGD	SGD	SGD	DGS

InterFET
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